

## INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

|  |  |           |  |
|--|--|-----------|--|
| (51) International Patent Classification <sup>6</sup> :<br><b>H01L 31/18, 31/232, H01J 3/14, G01J 3/51, G02B 5/20, G02F 1/1335</b> |  | <b>A1</b> | (11) International Publication Number: <b>WO 99/50914</b>      |
|  |  |           | (43) International Publication Date: 7 October 1999 (07.10.99) |

|   |   |
|---|---|
| <p>(21) International Application Number: PCT/US99/05439</p> <p>(22) International Filing Date: 12 March 1999 (12.03.99)</p> <p>(30) Priority Data:<br/>09/052,609                      31 March 1998 (31.03.98)                      US</p> <p>(71) Applicant (for all designated States except US): INTEL CORPORATION [US/US]; 2200 Mission College Boulevard, Santa Clara, CA 95052 (US).</p> <p>(72) Inventor; and</p> <p>(75) Inventor/Applicant (for US only): LI, Zong-Fu [CN/US]; 1326 Straford Avenue, Chandler, AZ 86233 (US).</p> <p>(74) Agents: TAYLOR, Edwin, H. et al.; Blakely, Sokoloff, Taylor &amp; Zafman LLP, 7th floor, 12400 Wilshire Boulevard, Los Angeles, CA 90025 (US).</p> | <p>(81) Designated States: AL, AM, AT, AT (Utility model), AU (Petty patent), AZ, BA, BB, BG, BR, BY, CA, CH, CN, CU, CZ, CZ (Utility model), DE, DE (Utility model), DK, DK (Utility model), EE, EE (Utility model), ES, FI, FI (Utility model), GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MD, MG, MK, MN, MW, MX, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SK (Utility model), SL, TJ, TM, TR, TT, UA, UG, US, UZ, VN, YU, ZW, ARIPO patent (GH, GM, KE, LS, MW, SD, SL, SZ, UG, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG).</p> <p><b>Published</b><br/>With international search report.<br/>Before the expiration of the time limit for amending the claims and to be republished in the event of the receipt of amendments.</p> |
|---|---|

(54) Title: COLOR MICROLENSSES AND A METHOD FOR CREATING

(57) Abstract

The making and use of microlenses (404, 408, 412) in color image sensors and color display devices (420, 428, 432, 436) is described. The color microlenses combine the function of a colorless microlens and a color filter into a single structure (404) for simplifying the fabrication of, and increasing the reliability of display devices and image sensors.

**FOR THE PURPOSES OF INFORMATION ONLY**

Codes used to identify States party to the PCT on the front pages of pamphlets publishing international applications under the PCT.

|    |                          |    |  |    |  |    |                          |
|----|--------------------------|----|--|----|--|----|--------------------------|
| AL | Albania                  | ES | Spain                                    | LS | Lesotho                                      | SI | Slovenia                 |
| AM | Armenia                  | FI | Finland                                  | LT | Lithuania                                    | SK | Slovakia                 |
| AT | Austria                  | FR | France                                   | LU | Luxembourg                                   | SN | Senegal                  |
| AU | Australia                | GA | Gabon                                    | LV | Latvia                                       | SZ | Swaziland                |
| AZ | Azerbaijan               | GB | United Kingdom                           | MC | Monaco                                       | TD | Chad                     |
| BA | Bosnia and Herzegovina   | GE | Georgia                                  | MD | Republic of Moldova                          | TG | Togo                     |
| BB | Barbados                 | GH | Ghana                                    | MG | Madagascar                                   | TJ | Tajikistan               |
| BE | Belgium                  | GN | Guinea                                   | MK | The former Yugoslav<br>Republic of Macedonia | TM | Turkmenistan             |
| BF | Burkina Faso             | GR | Greece                                   | ML | Mali   | TR | Turkey                   |
| BG | Bulgaria                 | HU | Hungary                                  | MN | Mongolia                                     | TT | Trinidad and Tobago      |
| BJ | Benin                    | IE | Ireland                                  | MR | Mauritania                                   | UA | Ukraine                  |
| BR | Brazil                   | IL | Israel                                   | MW | Malawi                                       | UG | Uganda                   |
| BY | Belarus                  | IS | Iceland                                  | MX | Mexico                                       | US | United States of America |
| CA | Canada                   | IT | Italy                                    | NE | Niger  | UZ | Uzbekistan               |
| CF | Central African Republic | JP | Japan                                    | NL | Netherlands                                  | VN | Viet Nam                 |
| CG | Congo                    | KE | Kenya                                    | NO | Norway                                       | YU | Yugoslavia               |
| CH | Switzerland              | KG | Kyrgyzstan                               | NZ | New Zealand                                  | ZW | Zimbabwe                 |
| CI | Côte d'Ivoire            | KP | Democratic People's<br>Republic of Korea | PL | Poland                                       |    |                          |
| CM | Cameroon                 | KR | Republic of Korea                        | PT | Portugal                                     |    |                          |
| CN | China                    | KZ | Kazakstan                                | RO | Romania                                      |    |                          |
| CU | Cuba                     | LC | Saint Lucia                              | RU | Russian Federation                           |    |                          |
| CZ | Czech Republic           | LI | Liechtenstein                            | SD | Sudan  |    |                          |
| DE | Germany                  | LK | Sri Lanka                                | SE | Sweden                                       |    |                          |
| DK | Denmark                  | LR | Liberia                                  | SG | Singapore                                    |    |                          |
| EE | Estonia                  |    |  |    |  |    |                          |

-1-

## COLOR MICROLENSSES AND A METHOD FOR CREATING

### FIELD

The present invention relates to the field of image sensors and display devices.

### GENERAL BACKGROUND

Microlenses have long been used in imaging devices to focus light on sensors including charge couple device (CCD) sensors and complementary metal oxide semiconductor (CMOS) sensors. The microlenses significantly improve the light sensitivity of the imaging device by collecting light from a large light collecting area and focusing it on a small light sensitive area of the sensor. The ratio of the overall light collecting area of a sensor to the light sensitive area of the sensor is defined to be a fill factor. Typical fill factors in prior art designs are less than 50%.

One prior art method of generating a color image signal is shown in Figure 1A. Light from a subject to be imaged comes in as light rays 104 and passes through a set of microlenses 108, 112, 116. The microlenses are formed on a planarization layer 120. After passing through the planarization layer 120, the light 104 is filtered by color filters 124, 128, 132 which together form a color filter array. Each color filter 124, 128, 132 in the color filter array only allows light of a specific color to pass through. A "color" is defined to be light having a specific range of frequencies. Typical color filters 124, 128, 132 used in the color filter array are red, green and blue filters (RGB) or cyan, magenta and yellow (CMY) filters. Each microlens and color filter combination corresponds to a sensor 136, 140, 144. Each sensor is a light sensitive device capable of converting the intensity of light striking the sensor 136, 140, 144 into an electrical signal. A microlens, color filter, and sensors such as sensors 136, 140, 144 correspond to a pixel of an image. The sensors 136, 140, 144 are in close proximity to each other, and each sensor receives filtered light from a corresponding color filter 124, 128, 132. By combining the output of the sensors 136, 140, 144, a processor, such as a graphics processor, can determine the approximate intensity and color of light striking the area in the proximity of sensor 136, 140, 144. By creating an array of such sensors

-2-

(red sensor 160, blue sensor 164, green sensor 168) as shown in Figure 1B, an overall color image can be reconstructed.

The fabrication of separate microlenses, color filters, and image sensors in the structure illustrated in Figures 1A and 1B has several disadvantages. For example, one disadvantage of the traditional structure is that many process steps are needed to form a first layer 148 including the sensors 136, 140, 144; a second layer 152 including the color filters 124, 128, 132, and a third planarization layer 156 to support microlenses 108, 112, 116.

Another disadvantage of the current structure is that the microlenses 108, 112, 116 are separated from the corresponding image sensors 136, 140, 144 by the planarization layer 156 and the color filter layer 152. The separation reduces the light reaching the sensors 136, 140, 144 because some light is absorbed passing through the multiple layers 152, 156. Furthermore, the separation results in increased crosstalk between pixels. "Crosstalk" results when off axis light strikes a microlens such as microlens 112 at an obtuse angle of incidence. The off-axis light passes through planarization layers 156 and a color filter 128 missing the sensor 140 which corresponds to the color filter 128 and instead striking an adjacent sensor 136. Alternately, the off-axis light coming in through microlens 112 may pass between filters 124 and 128 and reach adjacent sensor 136 resulting in an erroneous readings from the image sensor 136.

Additional disadvantages of the current micro-lens filter combinations include the additional process steps being used to fabricate the multi-level structure of Figure 1, the decreased reliability resulting from separation of layers 148, 152, 156 and the increased material costs used to fabricate separate transparent microlenses 108, 112, 116, color filters 124, 128, 132, and associated planarization layer 156.

A second use of the microlens, color filter layer, structure is in color display devices. Figure 2 illustrates an example of using the microlens color filter structure in a thin film transfer (TFT) liquid crystal display device. In Figure 2, light from a backlight or other light source 204 passes through a color filter layer 208 containing color filters 212, 216 and 220. The color filters 212, 216, 220 are typically different colors allowing only one color of light to pass through each filter. Microlenses 224, 228 and 232 in microlens layer 236 focuses the light from corresponding color filters 212, 216, 220 through a substrate 240 and a liquid crystal display (LCD) layer

-3-

244 to a TFT substrate 248. Each TFT switch 252, 256, 260 corresponds to a corresponding color filter 212, 216, 220. By controlling the amount of light passing through each switch 252, 256, 260, the output of each color filter 212, 216, 220 can be controlled. Combining the outputs of the color filters and TFT switches generates the output of a pixel of the color display device.

Display devices formed using the described techniques suffer from the previously described disadvantages including (1) difficulty in fabrication; (2) crosstalk between filters and switches caused by the increased separation generated by the microlens layer; and (3) problems with device reliability resulting from adhesion between multiple layers and increased material costs resulting from the necessity for multiple layers.

Thus an improved method for forming microlens and color filter structures is desired.

#### **Summary**

The present invention describes a method of forming a color microlens array on a semiconductor substrate. The method involves depositing a colored microlens resist on a semiconductor surface. The colored microlens resist is patterned and then baked to cause flowing of the colored microlens resist resulting in a color microlens with a curved surface.

#### **Brief Descriptions of the Drawings:**

Figure 1A is a cross section drawing of a conventional color filter array structure for acquiring color images.

Figure 1B illustrates an example of an arrangement of color filters in a detection device.

Figure 2 is a cross section of a thin film transfer (TFT) based liquid crystal display utilizing a microlens system.

Figure 3 illustrates a cross section of a color imaging device for acquiring color images utilizing a colored microlens array which combines microlenses and color filters.

Figure 4 is a cross section of a TFT liquid crystal display utilizing the color microlenses of the present invention.

Figure 5 shows the processes used in fabricating a colored microlens.

Figure 6A through 6E show the cross-section of a microlens system after key processing operations.

-4-

**Detailed Description:**

In the following description, an array of colored microlenses will be described. In the embodiment, the colored microlenses are formed over a planar substrate using semiconductor processing techniques, including photolithography and baking of a microlens resist. Combining the function of a microlens and a color filter into a single colored microlens reduces the number of components and number of operations used to fabricate color display and image acquisition devices. Reducing the number of components also increases device reliability. Examples of devices which utilize color microlenses include, but are not limited to, colored imaging displays, such as TFT displays, for example, and image acquisition devices such as charge coupled device (CCD) digital cameras.

In the accompanying description, certain details will be provided to facilitate understanding of the invention. For example, certain processes used to form the color microlenses are described. However it is recognized that other methods of fabricating a color microlens may be appropriate. The included details are provided to facilitate understanding of the invention and should not be interpreted to limit the scope of the invention. Certain details will be omitted because such detail would obscure the invention and are already well understood by those of ordinary skill in the art.

Figure 3 illustrates a set of microlenses 304, 308, 312 for use in a color imaging device. Light rays 316 from an external source passes through the colored microlenses 304, 308, 312 and are incident upon a set of sensors 320, 324 and 328. Each microlens 304, 308, 312 in the set typically allows a different color of light to pass through. Thus, in one embodiment, one microlens may be red, another blue and a third microlens green. Together, the set of three microlenses detect light corresponding to a pixel of an image. In this embodiment, the three microlenses 304, 308, 312 are located in close proximity to each other (typically within one micron), each microlens 304, 205, 312 positioned to allow one color of light to reach the sensor 320, 324, 328 corresponding to the microlens 304, 308, 342 respectively. A processor or other appropriate graphic circuitry can combine the output of the three sensors 320, 324, 328 to determine a color and intensity of light striking the general region around the three sensors 320, 324, 328. In an image, the general region corresponds to a pixel. To improve resolution, pixels should be small and, thus, the microlenses

-5-

should be small. The diameter of microlens ranges in size from 8 microns to 15 microns for different devices.

Figure 4 illustrates the use of color microlens 404, 408, 412 in a color display device. A light source 416 provides illumination which passes through microlenses 404, 408, 412 through a counter substrate layer 416 and to a liquid crystal display (LCD) layer 420. Each microlens of a set filters a different color, as well as focuses light from the light source 416 to a particular region of the LCD crystal layer 420 being switched. The crystals in the LCD under each color microlens act as a switch and filters that light. An applied electric potential determines when light can pass through the liquid crystal in the region underneath the microlens or when light is blocked from passing through the LCD layer 420. Electrodes residing on both sides of the LCD layer 420 are used to apply the electric potential.

In another embodiment, a thin film transfer (TFT) switch 428, 432, 436 may be used to switch the crystals in the LCD layer 420. The three microlenses 404, 408, 412 form a set corresponding to a color display device pixel. Thus, it is desired, but not required, that the microlenses 404, 408 and 412 have small dimensions, each microlens typically less than 10 microns in diameter by 3 microns in height so that they can be placed in close proximity. A human eye receives the output of the display device and merges the microlens outputs for a pixel to generate the actual color which is intended to be displayed.

Figure 5 is a flow diagram illustrating a lithographic method of fabricating color microlenses. In block 504 the surface of the semiconductor substrate upon which the microlenses will be formed is planarized. Planarization provides a flat and smooth substrate surface upon which a microlens resist can be deposited. In some embodiments, when a surface is already polished and smooth, planarization may be unnecessary. One method of planarization involves spin coating a planarization layer which is subsequently baked. The materials used in the spin coated planarization layer can be classified into either non-photo-definable and photo-definable materials. "Non-photo-definable" materials (non-photo-sensitive materials) include acrylics and polyorganosiloxane, for example. Examples of "photo-definable" materials (photo-sensitive materials) include acrylic based resists and epoxy based resists. In this embodiment, photo-definable planarization is used because non-photo-definable planarization often requires an extra photolithographic

-6-

patterning operation to open areas of bond pads, while photo-definable planarization layers can be patterned directly and etched.

In block 508, a color microlens resist material is deposited on the planarized surface. In one embodiment, deposition of the color microlens resist is achieved by spin coating a planarized layer with the color microlens resist. The thickness of the coating is determined by the required thickness of the microlens. The thickness of the microlens resist is a function of the focal length requirements of the microlens, a shorter focal length requires a thicker lens, and thus, a thicker microlens resist layer. The focal length of the microlens should be designed to effectively focus light on the corresponding sensor. The microlens thickness (t) vs. focal length (f) may be estimated according to the following relationship:

$$f = \left( \frac{3 At}{\pi (2 - \cos \Theta + \cos^3 \Theta)} \right)^{\frac{1}{3}} \left( \frac{n_1}{n_1 - n_o} \right)$$

where:

- A: Area of microlens
- $\Theta$ : Contact angle between microlens and supporting substrate
- $n_1$ : refractive index of microlens
- $n_o$ : refractive index of air

The "contact angle" is a function of the microlens curvature and can be computed as the angle between a first line tangent to the microlens surface at a point on the microlens near the interface between the microlens and the support substrate and a second line parallel to the support substrate surface. The contact angle is illustrated as angle  $\Theta$  450 of Figure 4.

The thickness and shape of the color microlens may be computed using ray tracing programs and is also dependent on the index of refraction of the microlens resist material. Different colored microlenses may contain different pigments having different indexes of refraction. Thus different microlenses in a set may have different dimensions. In typical sensor applications for which the pixel sizes are around 10 microns by 10 microns, the thickness of the microlens can vary from 2 to 4 microns depending on the index of refraction of the microlens material, the distance of the microlens from the sensor, and the area of the sensor. The



-7-

determination of lens shapes is well understood in the art and can be computed via commercially available rate tracing programs.

In block 512, the microlens resist is baked at a relatively low temperature known as a "soft bake". In a positive resist, the soft bake process involves baking the microlens resist at a temperature of about 100° Celsius (C) for a time of approximately one minute. After the soft bake, a patterning process is performed in which the microlens resist is typically exposed to ultraviolet (UV) light in a photolithographic process in block 516. In one embodiment the UV light has a wavelength or I-line of approximately 365 nanometers and dose of 100 Millijoules/cm<sup>2</sup>. After exposure to the UV light, the microlens resist is developed in a developer solution.

After the patterning block 516, the excess microlens resist material is removed leaving the appropriate amount of microlens resist to form a microlens. Typically, the structures remaining have an approximately square form. The square form is fixed using deep ultraviolet exposure, otherwise known as post-patterning flood exposure in block 520. The deep UV exposure causes cross-linking in the resist improving the transparency of the microlens resist material.

The shape of the microlens after post-patterning flood exposure is still a square form. In block 524, the microlens array is baked at a high temperature to cause the microlens resist to flow and form the desired curved shape. In one implementation of the invention, the microlens array is heated to a temperature of approximately 150°C for a predetermined period of time (e.g., approximately two minutes).

Blocks 508 through 524 are repeated for each different colored microlens to be deposited on a planarized surface. Thus if a red, green and blue microlens are to be formed on the planarized surface, three iterations of the operations set forth in blocks 508 through 524 are typically required, one iteration for the red microlens, a second iteration for the green microlens and a third iteration for the blue microlens. When in block 528, it is determined that the last microlens has been formed on the planarized surface, an optional silylating layer is formed over the microlenses in block 532.

Typically, the microlens array, formed in accordance with block 504 through 524, is a polymeric lens array and is formed from photoresists. However, prior to silylation, these polymeric microlenses formed from

-8-

photo resists lack the mechanical, thermal and environmental stability required for most devices. Thus, in this embodiment, the surface of the microlens array is silicated through silylation of the microlens resist. This silicated process is known to stabilize the resist and is described in literature such as Introduction to Microlithography edited by L. Thompson, C. Grant Wilson, and M.J. Bowden published by The American Chemical Society copyrighted 1994. On pages 243 to 244.

In one embodiment of the invention, the silylated microlens are further subject to deep ultraviolet bleaching. In the bleaching process, the microlens array is exposed to Deep (DUV) radiation of approximately 200 - 300 nanometers and intensity of 500 milliWatts/centimeter<sup>2</sup> wavelength for a period of one minute time such as that which occurs in Fusion DUV systems. The UV bleaching changes the light transmittance characteristics of the color microlenses. Bleaching reduces the tendency of the microlenses to have a yellowish tint.

In block 540, the silylated color microlens surface is converted to a silicated surface using an oxygen reactive ion treatment (RIE). A silicated surface is preferred to the silylated surface because the silicated surface is stiffer, more stable and resistant to deformation. In order to convert the silylated surface to a silicated surface, the silylated microlens surface is exposed to an oxygen reactive ion etch for approximately 30 seconds. The RIE etch power should be low enough such that it does not cause significant etching. A typical RIE etch power may be approximately 60 watts.

Figures 6A through 6D illustrate cross sections of the microlens structure at various stages in the processing described in Figure 5. In Figure 6A, the planarized surface 604 is shown with a deposited layer of color microlens resist 608. Figure 6B illustrates the "square" form of the remaining microlens resist 608 after the patterning block described in block 516. Figure 6C illustrates the patterned microlens resist during exposure to DUV radiation 612. In order to round angular edges, the color microlens resist is subject to a thermal flow or cross link baking process described in block 524 of Figure 5 to produce a curved microlens 608 as illustrated in Figure 6D. The color microlens resist, which now forms a color microlens of Figure 6D, is subject to silylated, DUV bleaching and RIE to produce the coated microlens structure 612 illustrated in Figure 6E.

-9-

While certain exemplary embodiments have been described in detail and shown in the accompanying drawings and description, it is to be understood that such embodiments are merely illustrative and not restrictive on the broad invention. This invention is not to be limited to the specific arrangement and constructions shown and described; since various other modifications may occur to those of ordinary skill in the art.

## CLAIMS

1. A method of forming a color microlens array on a semiconductor structure comprising:  
depositing a first colored microlens resist on a semiconductor surface;  
patterning the first colored microlens resist; and  
baking the first colored microlens resist to cause flowing of the first colored microlens resist resulting in at least one microlens with a curved surface.
2. The method of claim 1 further comprising :  
fixing the first colored microlens resist by deep ultra-violet exposure to cause cross-linking in the microlens resist after the patterning of the colored microlens resist.
3. The method of claim 1 further comprising:  
stabilizing the microlens surface using silylation of a surface of the first colored microlens.
4. The method of claim 1 further comprising repeating the depositing, patterning and baking operations on said semiconductor structure using a second colored microlens resist, said second microlens resist filtering a different color than said first colored microlens resist.
5. The method of claim 1 further comprising:  
exposing at least one microlens to a deep ultra-violet bleaching to improve transparency.
6. The method of claim 1 wherein the depositing, patterning, and baking operations are repeated three times, each time corresponding to a different colored polymer resist.
7. The method of claim 1 wherein the patterning operation is performed using a photolithographic process.

-11-

8. A color imaging acquisition device comprising:  
an array of light sensitive sensors; and  
an array of color microlenses, each microlens in the array of color microlenses corresponding to a light sensitive sensor in the array of light sensitive sensors and designed to filter a corresponding color of light.
9. The color image acquisition device of claim 8:  
wherein each microlens in the array of color microlens is an element in a corresponding set of microlenses, each microlens in each set filtering a different color of light.
10. The color image acquisition device of claim 8 wherein each microlens in the array of color microlenses is less than 15 microns in diameter.
11. The color acquisition device of claim 8 wherein the light sensitive sensors are charge coupled device sensors.
12. The color acquisition device of claim 8 wherein the light sensitive sensors are metal oxide semiconductor sensors.
13. The color acquisition device of claim 8 wherein a microlens of the array of the color microlenses is formed from a pigmented polymer.
14. A color display device comprising:  
a light source;  
a plurality of switches for controlling light from the light source;  
and  
a plurality of color microlens for focusing and filtering light from the light source and delivering the light from the light source to the plurality of switches.
15. The color display device of claim 14 wherein each switch of said plurality of switches is a region of a liquid crystal display layer.

-12-

16. The color display device of claim 14 wherein each microlens in said plurality of color microlenses corresponds to a switch in said plurality of switches.

17. The color display device of claim 14 wherein the plurality of color microlenses are organized into multiple sets of color microlens, each set of color microlenses including three microlenses from the plurality of color microlenses, each microlens in the set of microlenses for filtering a different colored light.

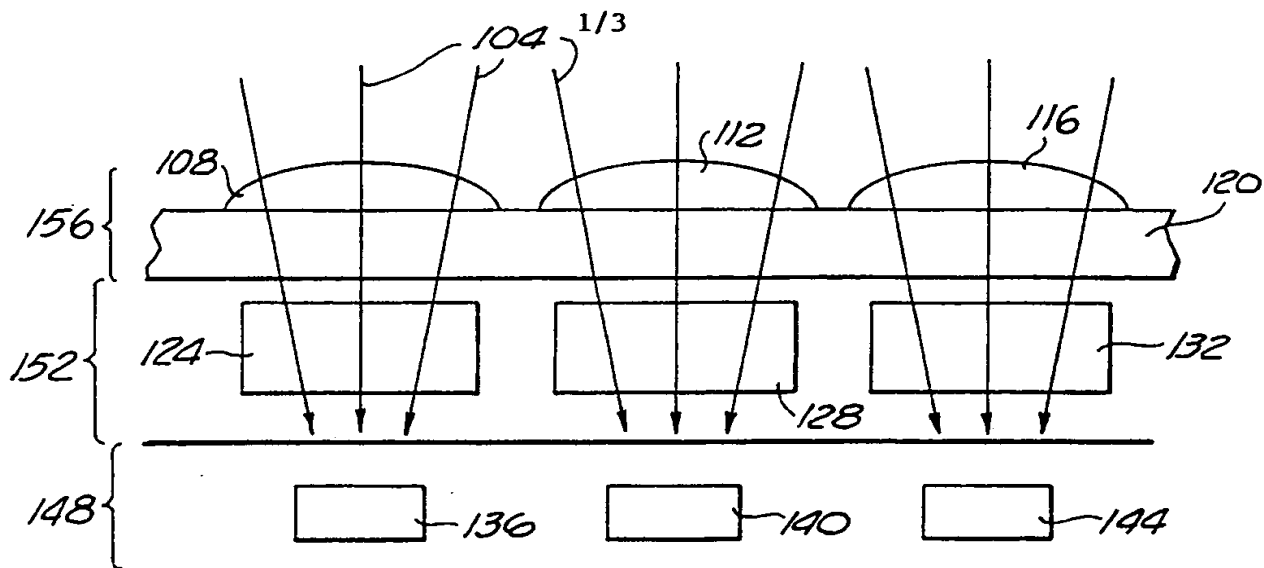


FIG. 1A (PRIOR ART)

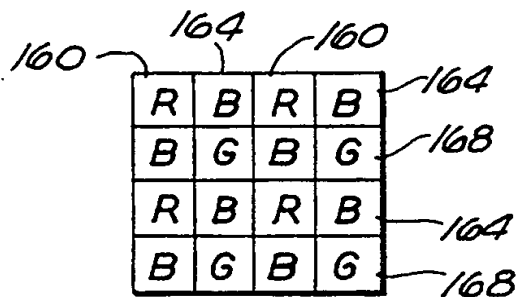


FIG. 1B

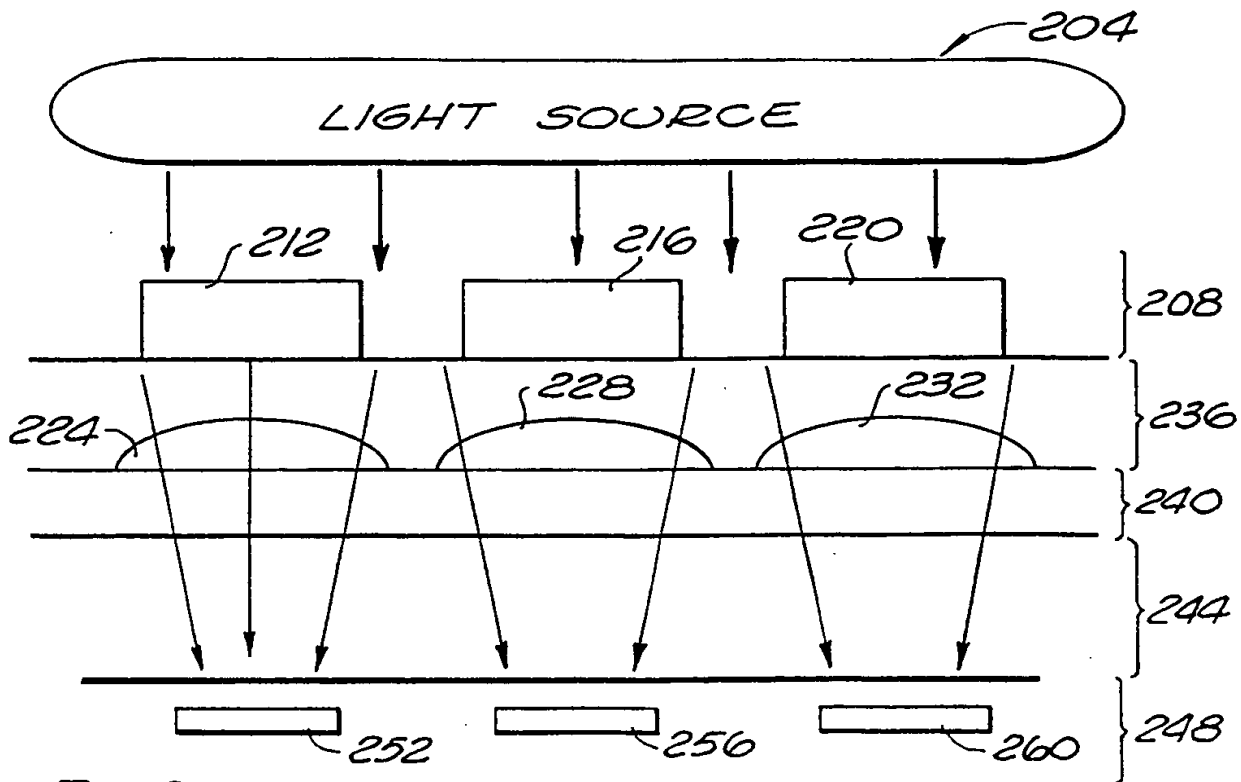


FIG. 2 (PRIOR ART)

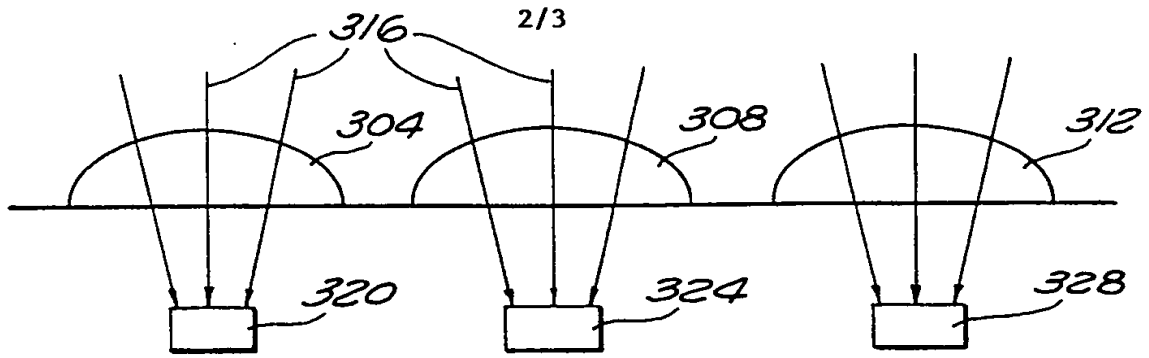


FIG. 3

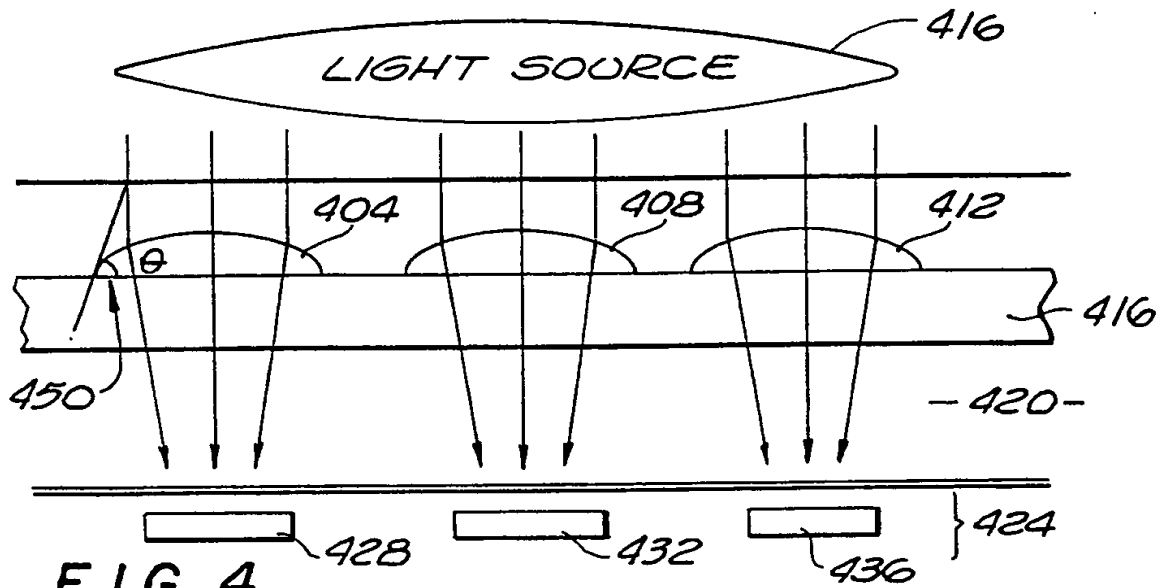


FIG. 4

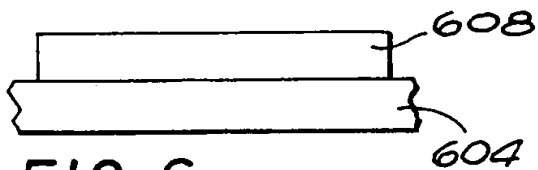


FIG. 6A

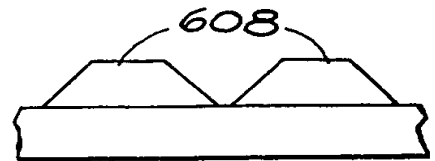


FIG. 6B

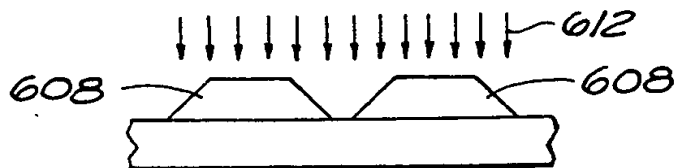


FIG. 6C

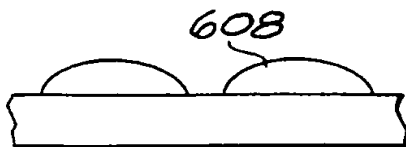


FIG. 6D

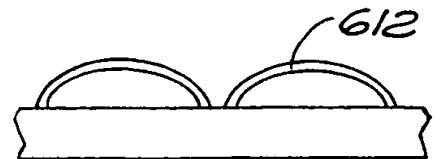
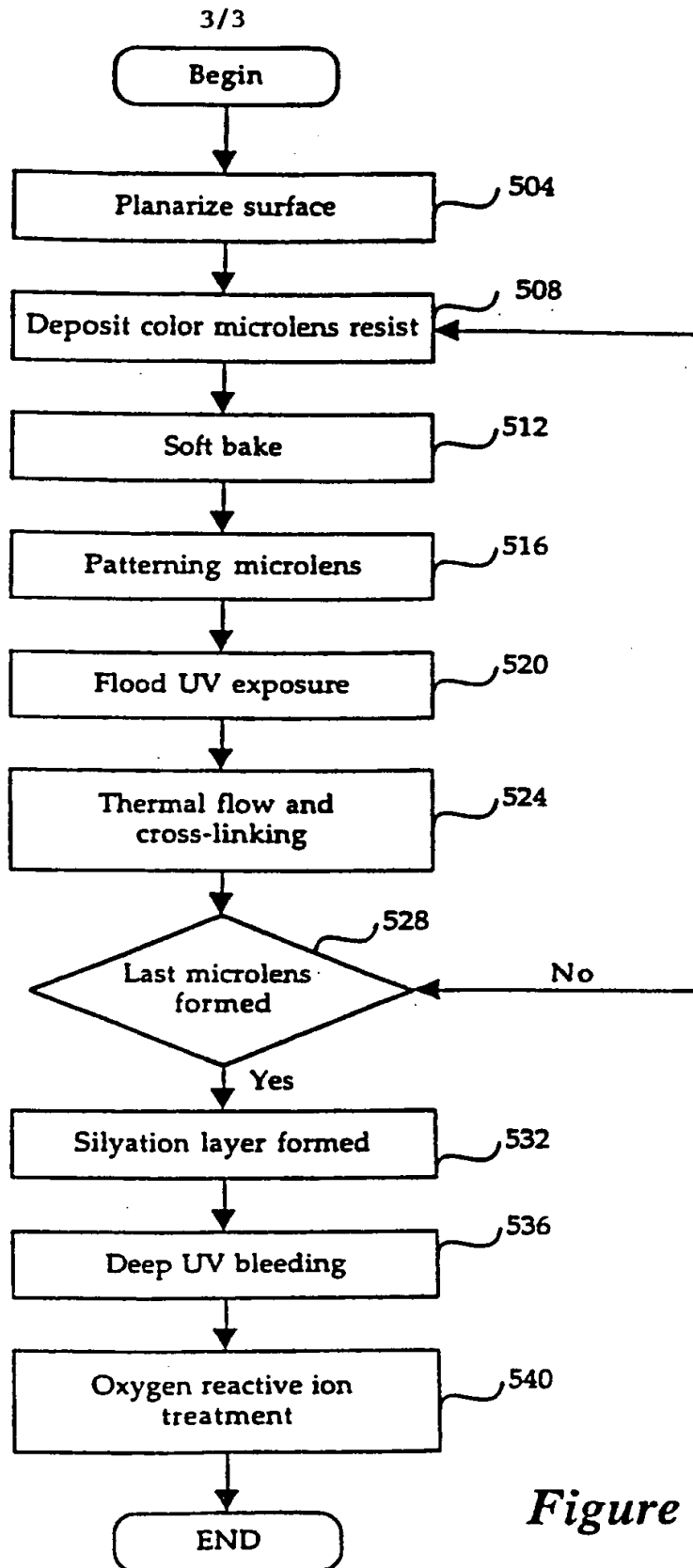


FIG. 6E



*Figure 5*

## INTERNATIONAL SEARCH REPORT

International application No.  
PCT/US99/05439

## A. CLASSIFICATION OF SUBJECT MATTER

IPC(6) : H01L 31/18, 232; H01J 3/14; G01J 3/51; G02B 5/20; G02F 1/1335.

US CL : 437/3, 53; 250/216, 226; 430/7; 349/95, 106.

According to International Patent Classification (IPC) or to both national classification and IPC

## B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

U.S. : 437/3, 53; 250/216, 226; 430/7; 349/95, 106.

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched  
NONEElectronic data base consulted during the international search (name of data base and, where practicable, search terms used)  
U.S. PTO APS SEARCH TERMS: ARRAY(4W)MICROLENS?, SENSORS, COLOR?(4W)MICROLENS? FILTER?  
CHARGED(2W)COUPLED(3W)DEVICE.

## C. DOCUMENTS CONSIDERED TO BE RELEVANT

| Category* | Citation of document, with indication, where appropriate, of the relevant passages                 | Relevant to claim No. |
|-----------|--|-----------------------|
| X         | US 5,677,200 A (PARK et al) 14 October 1997 (14/10/97). See columns 3-6 and figs. 2-4.             | 1-7                   |
| X         | US 5,466,926 A (SASANO et al) 14 November 1995 (14/11/95). See columns 2-6 and figure. 2A.         | 8-13                  |
| X         | US 5,682,215 A (NISHIHARA et al) 28 October 1997 (28/10/97). See columns 1-2 and 5-6 and figure 3. | 14-17                 |

☐ Further documents are listed in the continuation of Box C. ☐ See patent family annex.

|   |  |
|---|--|
| * Special categories of cited documents:  | *T* later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention  |
| *A* document defining the general state of the art which is not considered to be of particular relevance  | *X* document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone   |
| *E* earlier document published on or after the international filing date  | *Y* document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art |
| *L* document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified) | *Z* document member of the same patent family  |
| *O* document referring to an oral disclosure, use, exhibition or other means  |  |
| *P* document published prior to the international filing date but later than the priority date claimed  |  |

|   |  |
|---|--|
| Date of the actual completion of the international search<br>03 AUGUST 1999   | Date of mailing of the international search report<br>23 AUG 1999  |
| Name and mailing address of the ISA/US<br>Commissioner of Patents and Trademarks<br>Box PCT<br>Washington, D.C. 20231<br>Facsimile No. (703) 305-3230 | Authorized officer.<br>Dung Nguyen<br>Telephone No. (703) 305-0423 |

Form PCT/ISA/210 (second sheet)(July 1992)\*

## INTERNATIONAL SEARCH REPORT

International application No.

PCT/US99/05439

**Box I Observations where certain claims were found unsearchable (Continuation of item 1 of first sheet)**

This international report has not been established in respect of certain claims under Article 17(2)(a) for the following reasons:

1. ☐ Claims Nos.:  
because they relate to subject matter not required to be searched by this Authority, namely:
  
2. ☐ Claims Nos.:  
because they relate to parts of the international application that do not comply with the prescribed requirements to such an extent that no meaningful international search can be carried out, specifically:
  
3. ☐ Claims Nos.:  
because they are dependent claims and are not drafted in accordance with the second and third sentences of Rule 6.4(a).

**Box II Observations where unity of invention is lacking (Continuation of item 2 of first sheet)**

This International Searching Authority found multiple inventions in this international application, as follows:

Please See Extra Sheet.

1. ☒ As all required additional search fees were timely paid by the applicant, this international search report covers all searchable claims.
2. ☐ As all searchable claims could be searched without effort justifying an additional fee, this Authority did not invite payment of any additional fee.
3. ☐ As only some of the required additional search fees were timely paid by the applicant, this international search report covers only those claims for which fees were paid, specifically claims Nos.:
  
4. ☐ No required additional search fees were timely paid by the applicant. Consequently, this international search report is restricted to the invention first mentioned in the claims; it is covered by claims Nos.:

Remark on Protest

☐

The additional search fees were accompanied by the applicant's protest.

☒

No protest accompanied the payment of additional search fees.

# INTERNATIONAL SEARCH REPORT

International application No.  
PCT/US99/05439

## BOX II. OBSERVATIONS WHERE UNITY OF INVENTION WAS LACKING

This ISA found multiple inventions as follows:

This application contains the following inventions or groups of inventions which are not so linked as to form a single inventive concept under PCT Rule 13.1. In order for all inventions to be searched, the appropriate additional search fees must be paid.

Group I, claims 1-7, drawn to a method of forming a color microlens array on a semiconductor structure, classified in class 437, subclass 3.

Group II, claims 8-13, drawn to a color imaging acquisition device having array of sensors and array of color microlenses, classified in class 250, subclass 216.

Group III, claims 14-17, drawn to a color display device having a plurality of switches for controlling light from a light source, and a plurality of color microlens, classified in class 349, subclass 95.

The inventions listed as Groups I-III do not relate to a single inventive concept under PCT Rule 13.1 because, under PCT Rule 13.2, they lack the same or corresponding special technical features for the following reasons:

First, each of the color imaging acquisition device as defined in Group II and the color display device having switches as defined in Group III can be made by a method which is different from the method for making the microlens array as defined in Group I;

Second, the device as defined in Group III contains features which are not defined in the device of Group II. For instance, the device of Group II does not need a set of switches for controlling the light from a light source as defined in the device of Group III, and the device of the Group III does not need to have a charged-coupled device or a sensor system as defined in the device of Group II.